

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max (Note 10) T _C = +25°C
40V	3.0mΩ @ V _{GS} = 10V	100A
	5.0mΩ @ V _{GS} = 5V	93A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor controls
- DC-DC converters
- Power managements

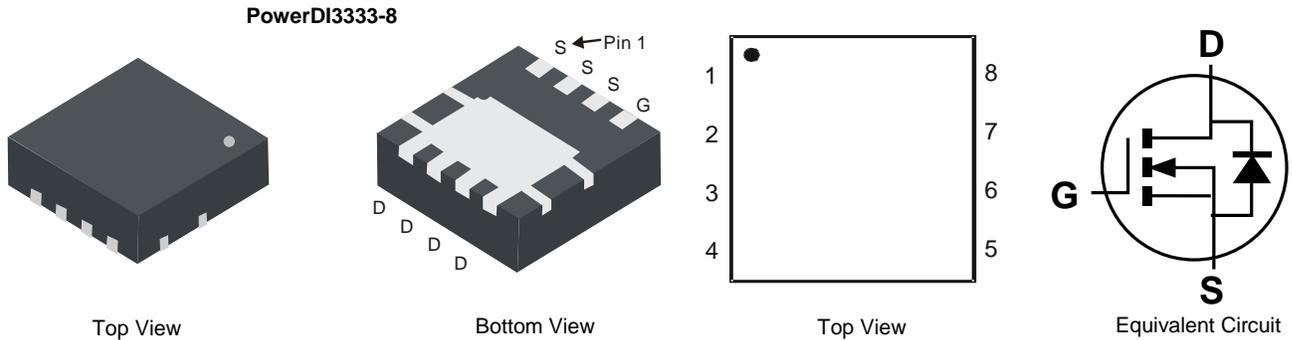
Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching, Test in Production – Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} – Ensures On-State Losses are Minimized
- Excellent Q_{GD} × R_{DS(ON)} Product (FOM)
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMTH43M8LFGQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: PowerDI[®]3333-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.034 grams (Approximate)



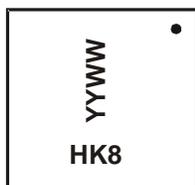
Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMTH43M8LFGQ-7	PowerDI3333-8	2,000	Tape & Reel
DMTH43M8LFGQ-13	PowerDI3333-8	3,000	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

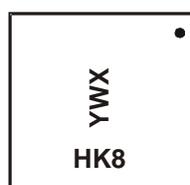
Marking Information

Site 1:



HK8 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 23 = 2023)
WW = Week Code (01 to 53)

Site 2:



HK8 = Product Type Marking Code
YWX = Date Code Marking
Y = Year Code (ex: 3 = 2023)
W = Week Code (ex: a = Week 27,
z Represents Week 52 and 53)
X = Internal Code (ex: U = Monday)

Maximum Ratings (@T_c = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	40	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 7) (Note 10) V _{GS} = 10V	I _D	100 85	A
Continuous Drain Current (Note 6) V _{GS} = 10V	I _D	24.0 16.9	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	400	A
Maximum Continuous Body Diode Forward Current (Note 7) (Note 10)	I _S	100	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	400	A
Avalanche Current, L = 1mH	I _{AS}	18.2	A
Avalanche Energy, L = 1mH	E _{AS}	165	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P _D	2.62	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	57.8	°C/W
Total Power Dissipation (Note 7)	P _D	65.2	W
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	2.3	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_J = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	40	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 32V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1	1.5	2.5	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	2.3	3.0	mΩ	V _{GS} = 10V, I _D = 20A
		—	3.4	5.0		V _{GS} = 5V, I _D = 15A
Static Drain-Source On-Resistance (T _J = +175°C) (Note 9)	R _{DS(ON)}	—	—	6.0	mΩ	V _{GS} = 10V, I _D = 20A
		—	—	9.0		V _{GS} = 5V, I _D = 15A
Diode Forward Voltage	V _{SD}	—	0.8	1.0	V	V _{GS} = 0V, I _S = 20A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	2798	—	pF	V _{DS} = 20V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	904	—		
Reverse Transfer Capacitance	C _{rss}	—	88	—		
Gate Resistance	R _g	—	2.44	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	40.1	—	nC	V _{DS} = 20V, I _D = 20A, V _{GS} = 10V
Gate-Source Charge	Q _{gs}	—	5.2	—		
Gate-Drain Charge	Q _{gd}	—	8.8	—		
Turn-On Delay Time	t _{D(ON)}	—	5.16	—	ns	V _{DD} = 20V, V _{GS} = 10V, R _G = 1.6Ω, I _D = 20A
Turn-On Rise Time	t _r	—	10.7	—		
Turn-Off Delay Time	t _{D(OFF)}	—	24.6	—		
Turn-Off Fall Time	t _f	—	12.4	—		
Body Diode Reverse Recovery Time	t _{RR}	—	32.6	—	ns	I _F = 15A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	—	26.6	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.
 - Package limit.

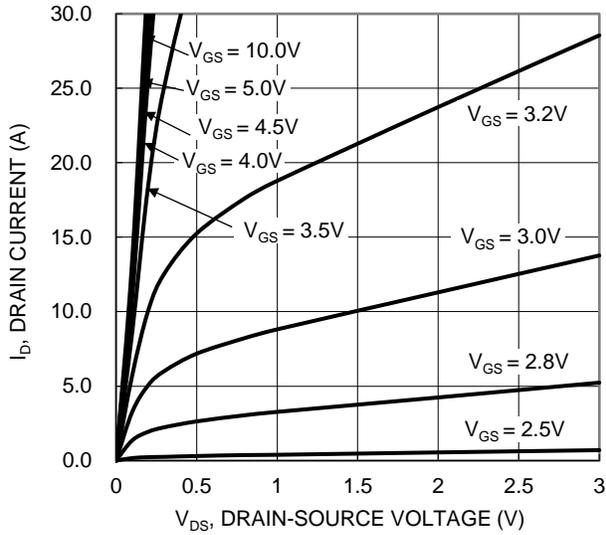


Figure 1. Typical Output Characteristic

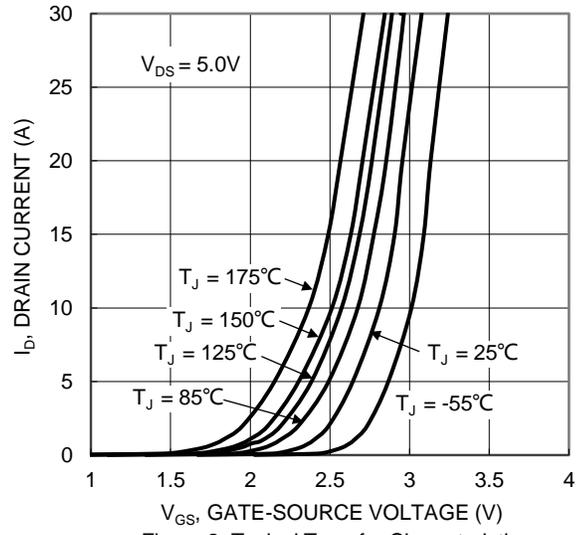


Figure 2. Typical Transfer Characteristic

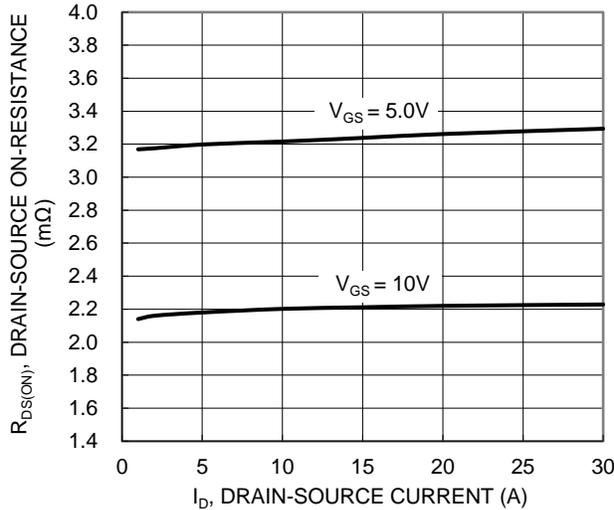


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

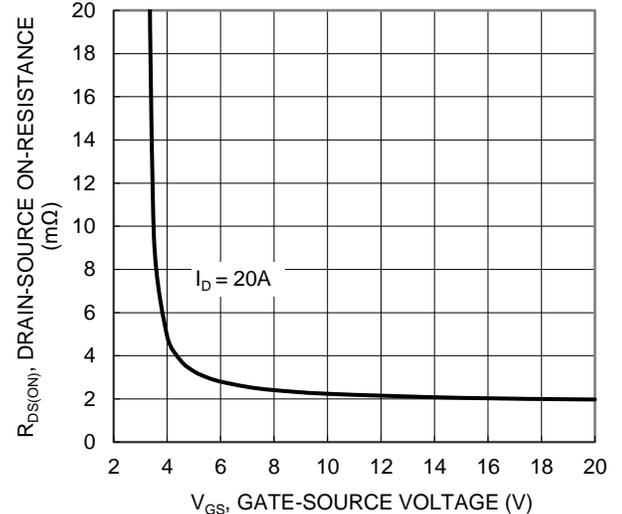


Figure 4. Typical Transfer Characteristic

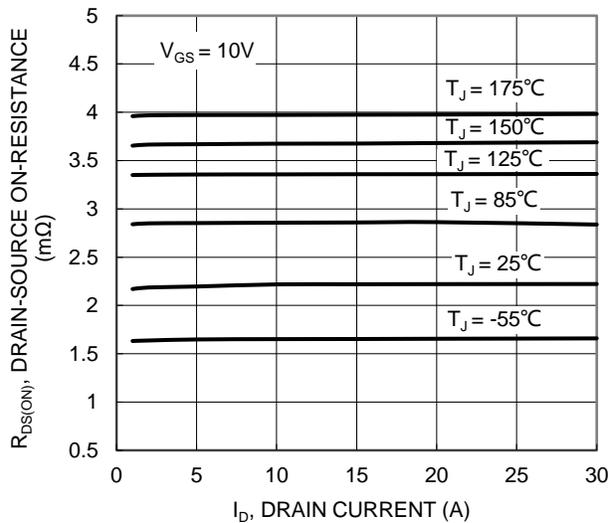


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

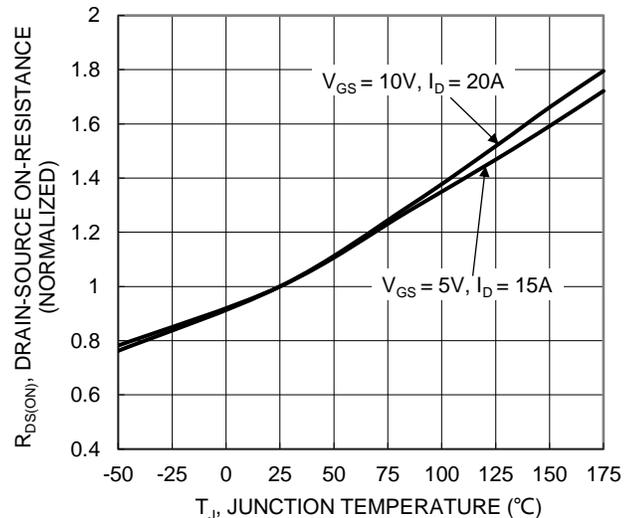


Figure 6. On-Resistance Variation with Temperature

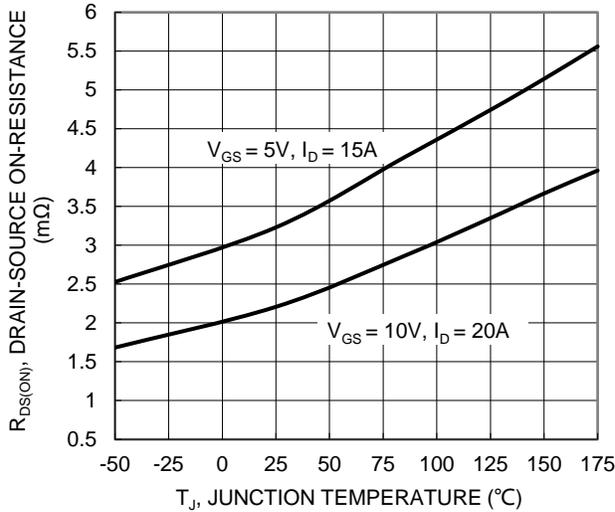


Figure 7. On-Resistance Variation with Temperature

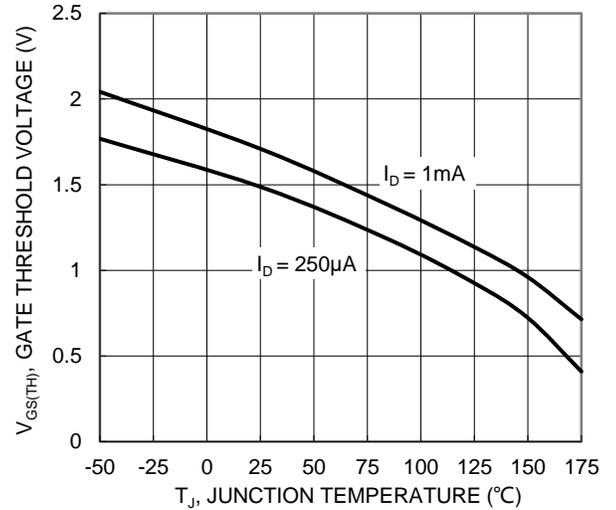


Figure 8. Gate Threshold Variation vs. Junction Temperature

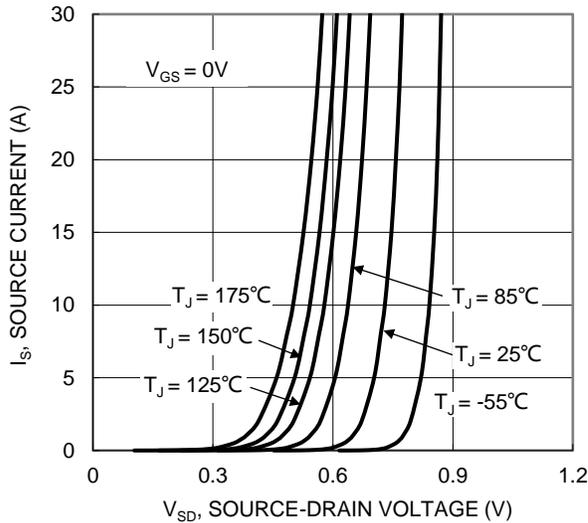


Figure 9. Diode Forward Voltage vs. Current

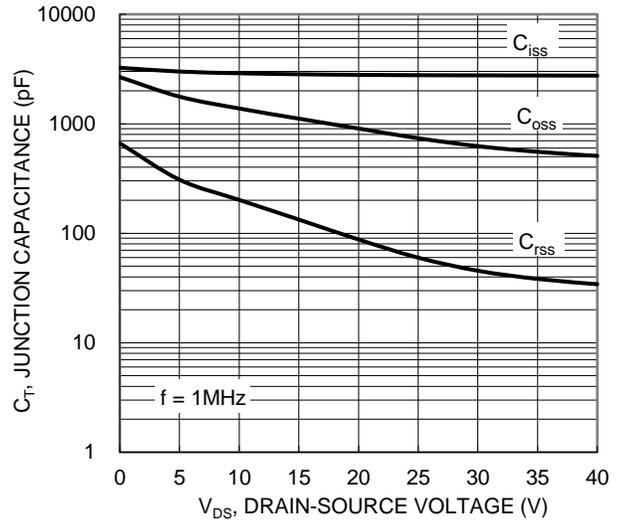


Figure 10. Typical Junction Capacitance

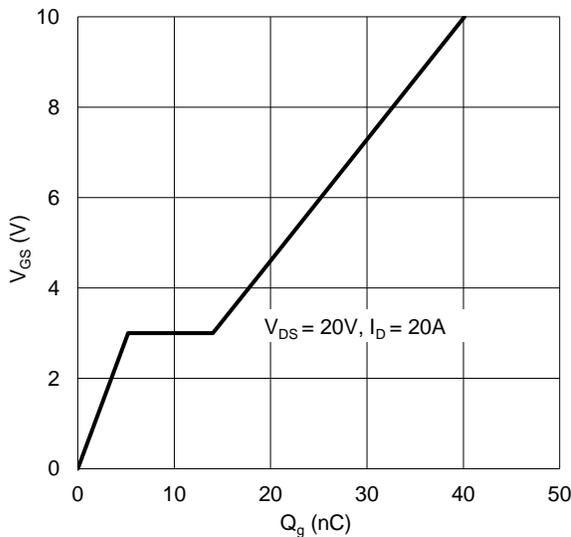


Figure 11. Gate Charge

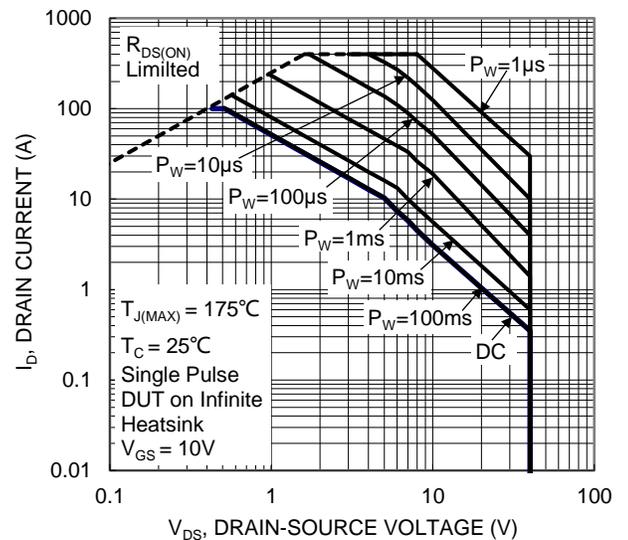
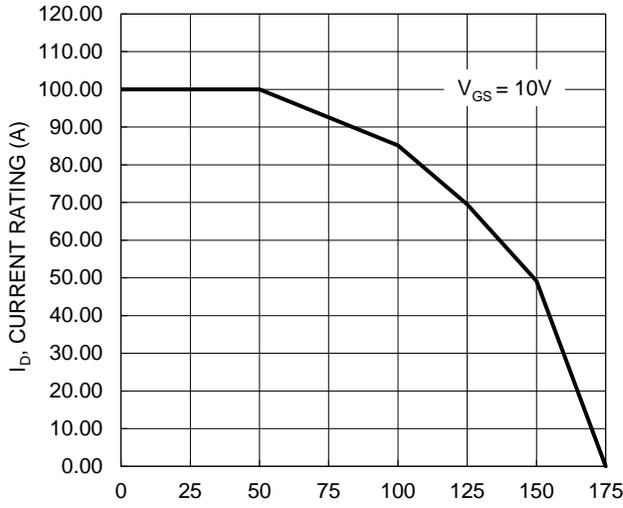
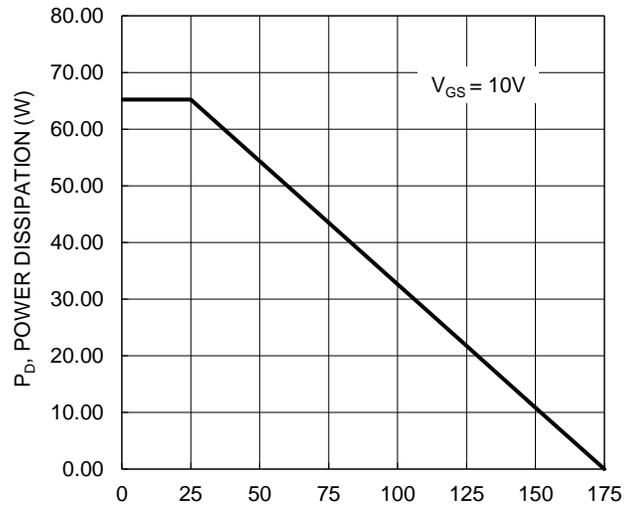


Figure 12. SOA, Safe Operation Area



T_c , CASE TEMPERATURE (°C)
Figure 13. Current Function of T_c



T_c , CASE TEMPERATURE (°C)
Figure 14. Power Dissipation Function of T_c

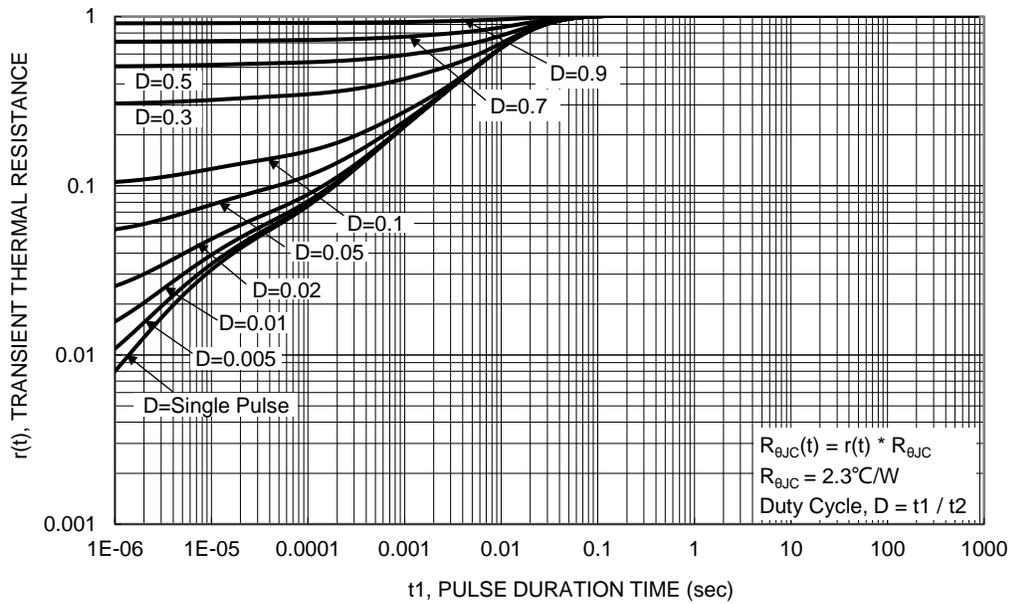


Figure 15. Transient Thermal Resistance

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